Vishay Semiconductors

1200 V Power SiC Gen 3 Merged PIN Schottky Diode, 5 A



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS									
l _F	5 A								
V _R	1200 V								
V _F at I _F at 25 °C, typ.	1.35 V								
T _J max.	175 °C								
I _R at V _R at 175 °C	3 μΑ								
Q _C (V _R = 800 V)	28 nC								
Package	TO-220AC 2L								
Circuit configuration	Single								

FEATURES

- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved V_F and efficiency by thin wafer $\begin{array}{c} \textbf{RoHS} \\ \textbf{COMPLIANT} \\ \textbf{COMPLIANT} \end{array}$
- Positive V_F temperature coefficient for easy paralleling
 HALOGEN
 FREE
- · Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 1200 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V _{RRM}		1200	V					
Continuous forward current	I _F ⁽¹⁾	$I_{\rm F}^{(1)}$ T _C = 152 °C (DC)		А					
Continuous forward current	I _F ⁽²⁾	T _C = 157 °C (DC)	5	A					
DC blocking voltage	V _{DC}		1200	V					
Repetitive peak forward current	I _{FRM}	T_{C} = 25 °C, f = 50 Hz, square wave, DC = 25 %	27	А					
	I _{FSM}	$T_{C} = 25 \text{ °C}, t_{p} = 10 \text{ ms}, \text{ half sine wave}$	42	٨					
Non-repetitive peak forward surge current		$T_C = 110 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	39	A					
	P _{tot} ⁽¹⁾	T _C = 25 °C	60	W					
Power dissipation		T _C = 110 °C	26	vv					
Fower dissipation	P _{tot} ⁽²⁾	T _C = 25 °C	79	W					
	rtot (−)	T _C = 110 °C	34	vv					
l ² t value	∫i ² dt	T _C = 25 °C	8.7	A ² s					
		T _C = 110 °C	7.6	A-S					
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C					

Notes

⁽¹⁾ Based on maximum R_{th}

⁽²⁾ Based on typical R_{th}

 $^{(3)}$ The heat generated must be less than the thermal conductivity from junction-to-ambient: dP_D/dT_J < 1/R_{0JA}

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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
		I _F = 5 A	-	1.35	1.5					
Forward voltage	V _F	I _F = 5 A, T _J = 150 °C	1.73	2.0	V					
		I _F = 5 A, T _J = 175 °C	-	1.85	-					
	I _R	$V_R = V_R$ rated	-	0.3	30					
Reverse leakage current		$V_R = V_R$ rated, $T_J = 150 \ ^\circ C$	-	2.0	80					
		$V_R = V_R$ rated, $T_J = 175 \text{ °C}$	3	-]					
Total conscitance	С	V _R = 1 V, f = 1 MHz	-	307	-	рF				
Total capacitance	U	V _R = 800 V, f = 1 MHz	-	20	-	pr				
Total capacitive charge	Q _C	V _R = 800 V, f = 1 MHz	-	28	-	nC				

THERMAL - MECHANICAL SPECIFICATIONS ($T_A = 25 \text{ °C}$ unless otherwise specified)										
PARAMETER	RAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS									
Thermal resistance, junction-to-case	R _{thJC}		-	1.9	2.50	°C/W				
Marking device		3C05ET12T								

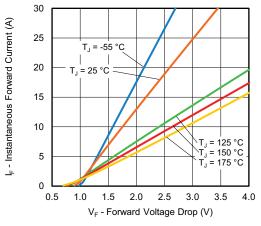


Fig. 1 - Typical Forward Voltage Drop Characteristics

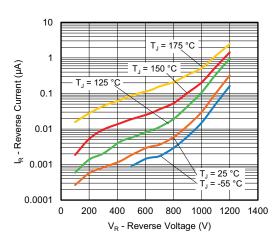


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

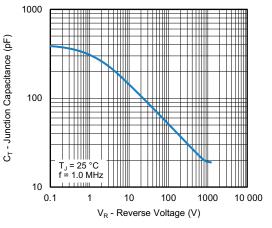


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

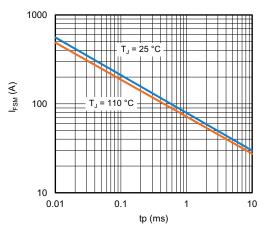
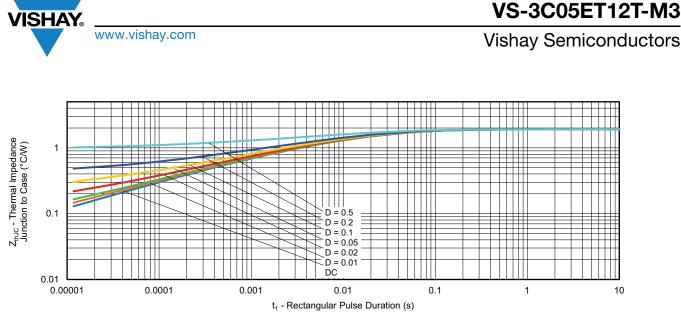


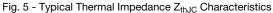
Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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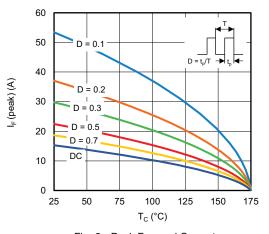


Fig. 6 - Peak Forward Current vs. Maximum Allowable Case Temperature

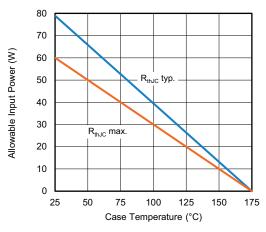


Fig. 7 - Forward Power Loss Characteristics

20 15 Capacitive Energy (µJ) 10 T_ = 25 °C 5 C V dV $E_I =$ 0 0 200 400 600 800 1000 1200 Reverse Voltage (V)

Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

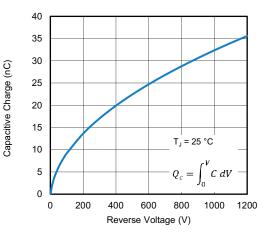


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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ORDERING INFORMATION TABLE

Device code	VS-	3C	05	Е	т	12	т	-M3
		2	3	4	5	6	7	8
	1	- Visl	nay Sem	niconduo	ctors pr	oduct		
	2	- 3C	= SiC di	iode, Ge	eneratio	n 3		
	3	- Cur	rent rati	ng (05 =	= 5 A)			
	4	- E=	single c	liode				
	5	- Pac	kage T	D-220				
	6	- Vol	tage rati	ng: (12	= 1200	V)		
	7	- T=	true 2 p	in				
	8	- Env	rironmer	ntal digit	:			
		-M3	3 = halog	gen-free	e, RoHS	-compli	ant, and	d termin

ORDERING INFORMATION		
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION
VS-3C05ET12T-M3	50/tube	Antistatic plastic tubes

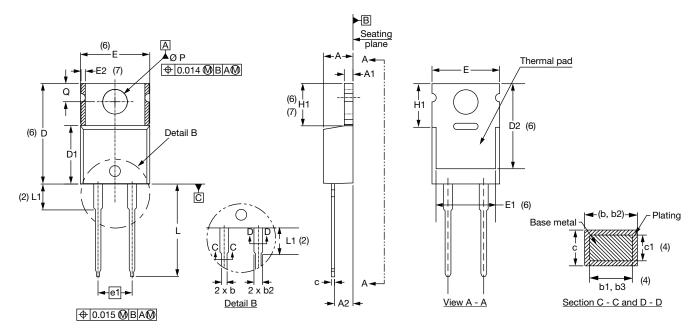
LINKS TO RELATED DOCUMENTS							
Dimensions www.vishay.com/doc?96069							
Part marking information	www.vishay.com/doc?95391						



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TO-220AC 2L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			e1	4.88	5.28	0.192	0.208	
b	0.69	1.01	0.027	0.040			H1	5.84	6.86	0.230	0.270	6, 7
b1	0.38	0.97	0.015	0.038	4		L	13.52	14.02	0.532	0.552	
b2	1.20	1.73	0.047	0.068			L1	3.32	3.82	0.131	0.150	2
b3	1.14	1.73	0.045	0.068	4		ØΡ	3.54	3.73	0.139	0.147	
с	0.36	0.61	0.014	0.024			Q	2.60	3.00	0.102	0.118	
c1	0.36	0.56	0.014	0.022	4							
D	14.85	15.25	0.585	0.600	3							
D1	8.38	9.02	0.330	0.355								
D2	11.68	12.88	0.460	0.507	6							
E	10.11	10.51	0.398	0.414	3, 6							

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

⁽⁵⁾ Controlling dimension: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1

⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed

⁽⁸⁾ Outline conforms to JEDEC[®] TO-220, except D2, where JEDEC[®] minimum is 0.480"

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